

IRLML0030TRPbF

V_{DS}	30	V
$V_{GS Max}$	± 20	V
$R_{DS(on) max}$ (@ $V_{GS} = 10V$)	27	mΩ
$R_{DS(on) max}$ (@ $V_{GS} = 4.5V$)	40	mΩ

FEATURES

- Low $R_{DS(on)}$ ($\leq 27m\Omega$)
- Industry-standard pinout
- Compatible with existing Surface Mount Techniques
- RoHS compliant containing no lead, no bromide and no halogen
- MSL1, Industrial qualification

Benefits

- Lower switching losses
- Multi-vendor compatibility
- Easier manufacturing
- Environmentally friendly
- Increased reliability

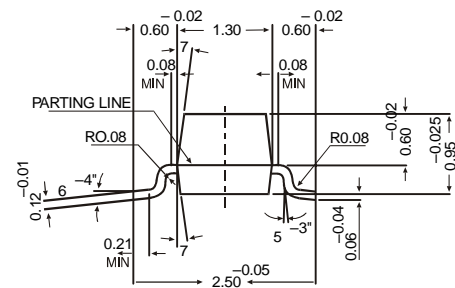
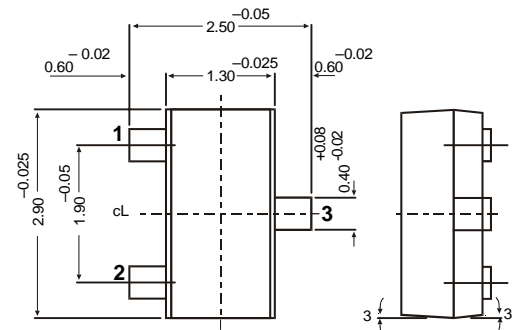
Application(s)

- Load/ System Switch

Marking: N55G



SOT-23 Formed SMD Package



Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V_{DS}	Drain-Source Voltage	30	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	5.3	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	4.3	
I_{DM}	Pulsed Drain Current	21	
$P_D @ T_A = 25^\circ C$	Maximum Power Dissipation	1.3	W
$P_D @ T_A = 70^\circ C$	Maximum Power Dissipation	0.8	
	Linear Derating Factor	0.01	
V_{GS}	Gate-to-Source Voltage	± 20	V
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient ^③	—	100	°C/W
$R_{\theta JA}$	Junction-to-Ambient (t<10s)	—	99	

Electric Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.02	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	33	40	$m\Omega$	$V_{GS} = 4.5V, I_D = 4.2A$ ②
		—	22	27		$V_{GS} = 10V, I_D = 5.2A$ ②
$V_{GS(th)}$	Gate Threshold Voltage	1.3	1.7	2.3	V	$V_{DS} = V_{GS}, I_D = 25\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	1	μA	$V_{DS} = 24V, V_{GS} = 0V$
		—	—	150		$V_{DS} = 24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
R_G	Internal Gate Resistance	—	2.3	—	Ω	
g_{fs}	Forward Transconductance	9.5	—	—	S	$V_{DS} = 10V, I_D = 5.2A$
Q_g	Total Gate Charge	—	2.6	—	nC	$I_D = 5.2A$
Q_{gs}	Gate-to-Source Charge	—	0.8	—		$V_{DS} = 15V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	1.1	—		$V_{GS} = 4.5V$ ②
$t_{d(on)}$	Turn-On Delay Time	—	5.2	—	ns	$V_{DD} = 15V$ ②
t_r	Rise Time	—	4.4	—		$I_D = 1.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	7.4	—		$R_G = 6.8\Omega$
t_f	Fall Time	—	4.4	—		$V_{GS} = 4.5V$
C_{iss}	Input Capacitance	—	382	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	84	—		$V_{DS} = 15V$
C_{riss}	Reverse Transfer Capacitance	—	39	—		$f = 1.0\text{MHz}$

Source - Drain Ratings and Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	1.6	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	21		
V_{SD}	Diode Forward Voltage	—	—	1.0	V	$T_J = 25^\circ\text{C}, I_S = 1.6A, V_{GS} = 0V$ ②
t_{rr}	Reverse Recovery Time	—	11	17	ns	$T_J = 25^\circ\text{C}, V_R = 15V, I_F = 1.6A$
Q_{rr}	Reverse Recovery Charge	—	4.0	6.0	nC	$di/dt = 100A/\mu s$ ②

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.
- ③ Surface mounted on 1 in square Cu board

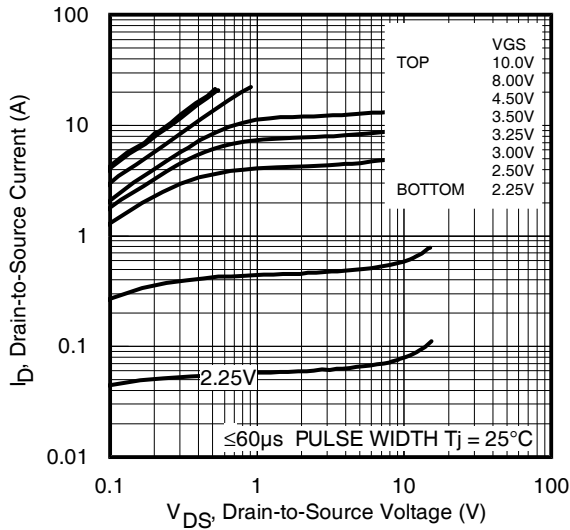


Fig 1. Typical Output Characteristics

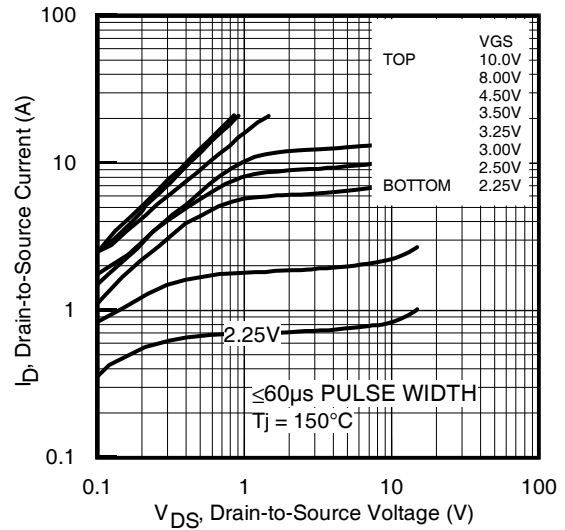


Fig 2. Typical Output Characteristics

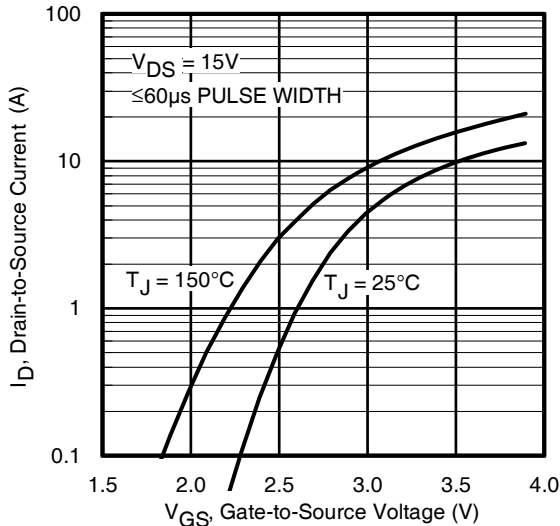


Fig 3. Typical Transfer Characteristics

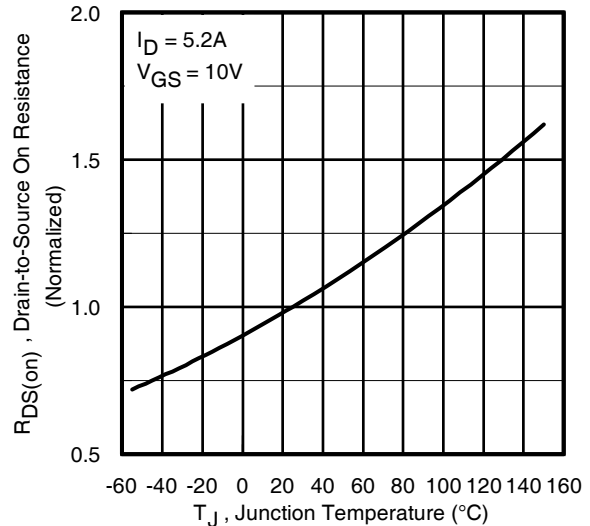


Fig 4. Normalized On-Resistance Vs. Temperature

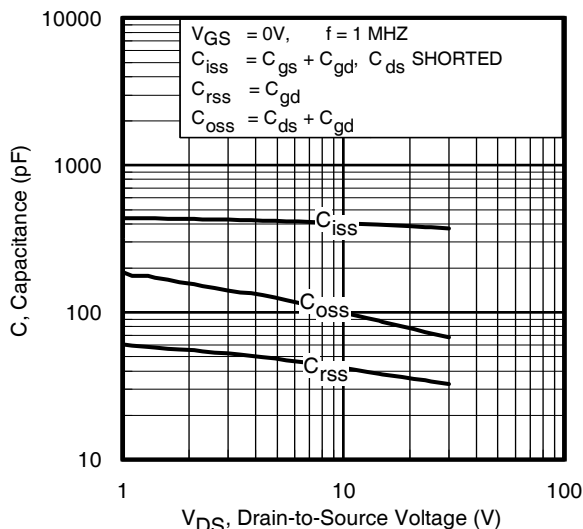


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

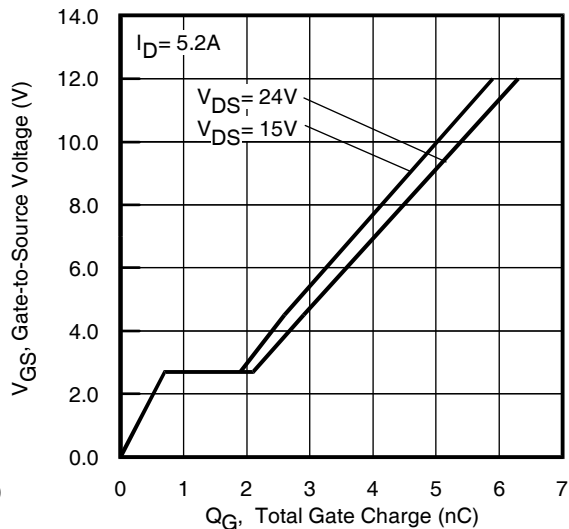


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

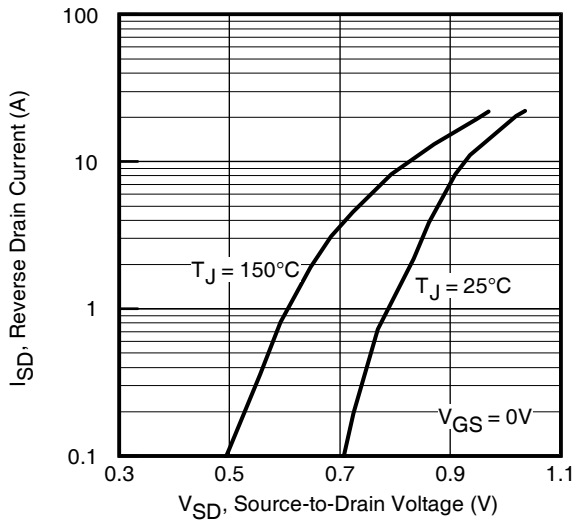


Fig 7. Typical Source-Drain Diode Forward Voltage

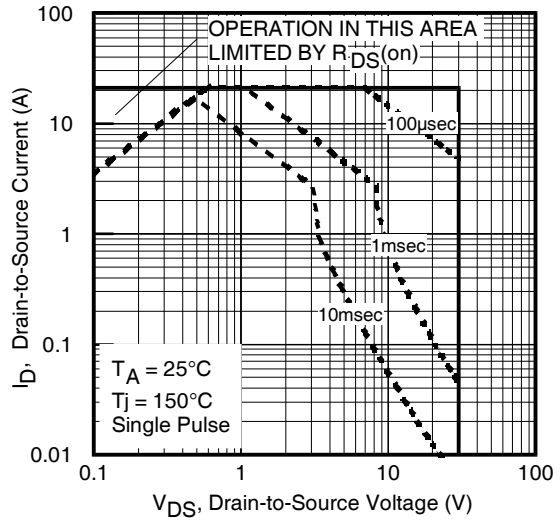


Fig 8. Maximum Safe Operating Area

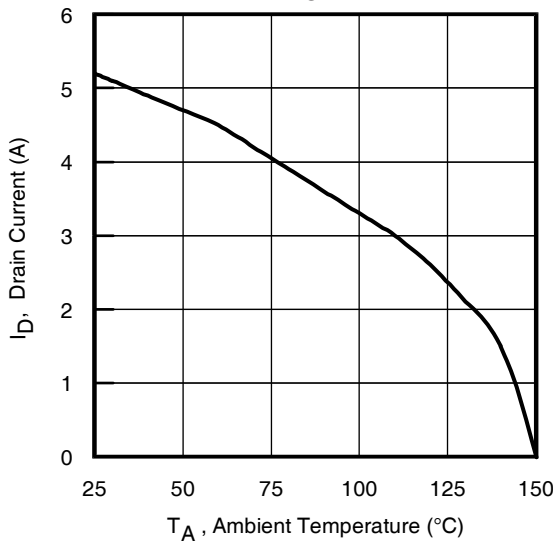


Fig 9. Maximum Drain Current Vs. Ambient Temperature

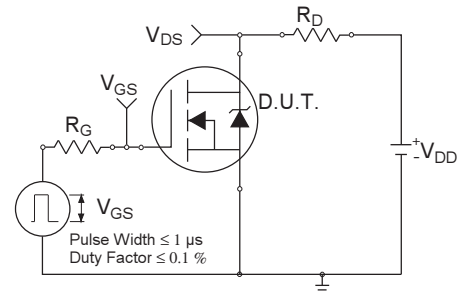


Fig 10a. Switching Time Test Circuit

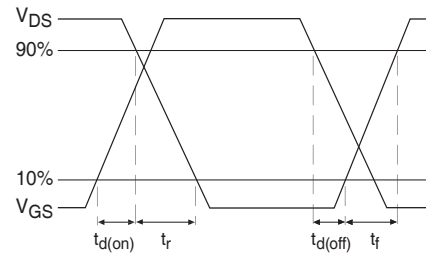


Fig 10b. Switching Time Waveforms

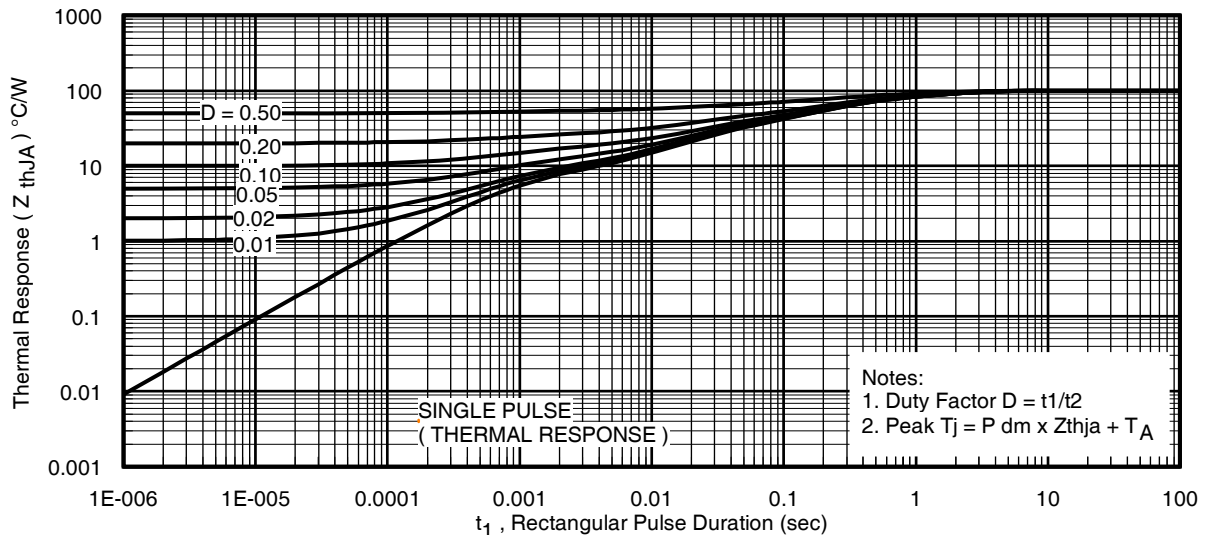


Fig 11. Typical Effective Transient Thermal Impedance, Junction-to-Ambient

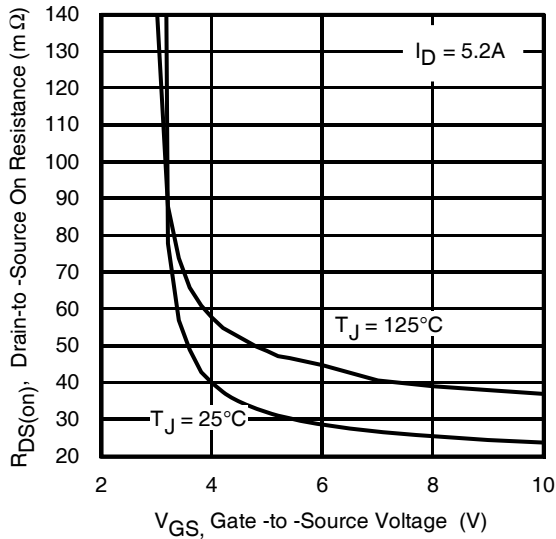


Fig 12. Typical On-Resistance Vs. Gate Voltage

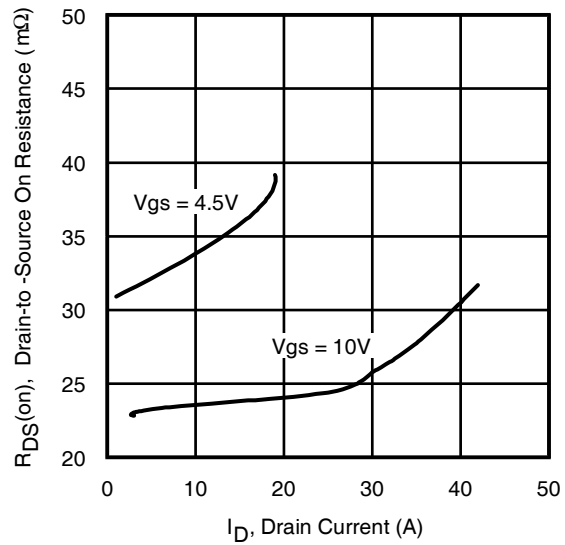


Fig 13. Typical On-Resistance Vs. Drain Current

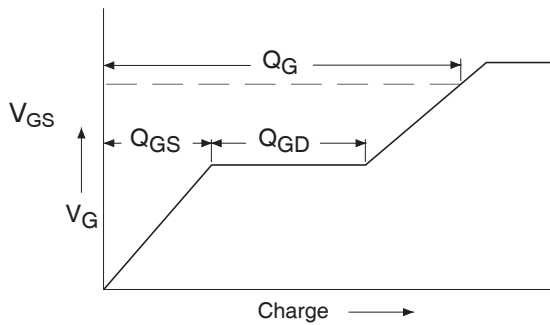


Fig 14a. Basic Gate Charge Waveform

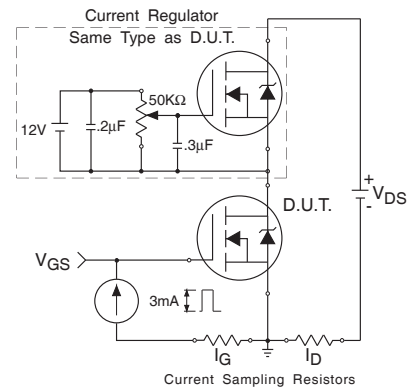


Fig 14b. Gate Charge Test Circuit

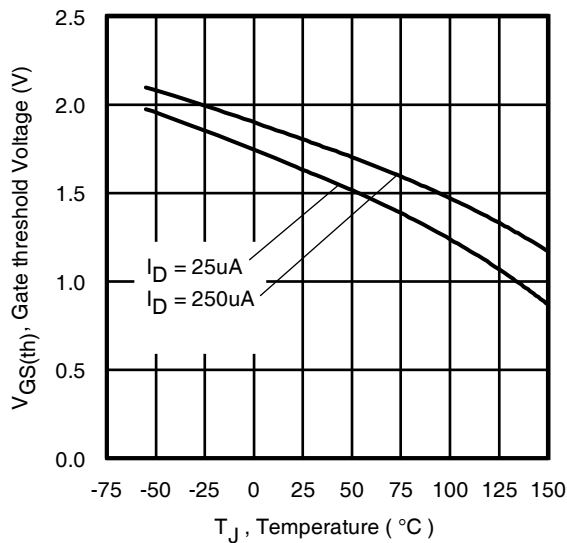


Fig 15. Typical Threshold Voltage Vs. Junction Temperature

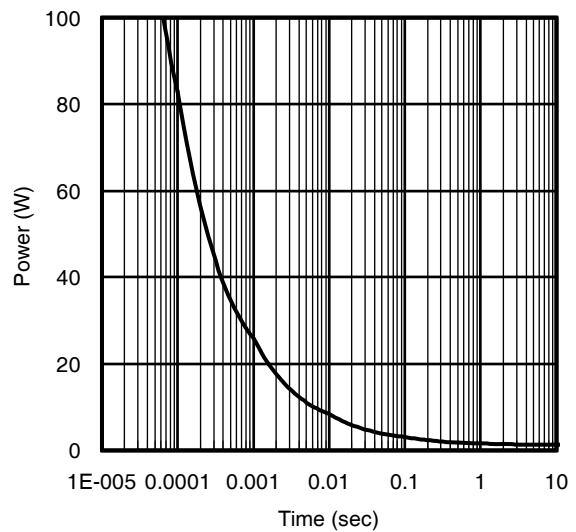


Fig 16. Typical Power Vs. Time